

SAM™ Data Sheet SAM-1064-40-9ps-x, λ = 1064 nm

| High reflection band λ | . = 1000 1100 nm |
|--------------------------------|---|
| Absorbance A | $A_0 = 40 \%$ |
| Modulation depth | ∆R = 25 % |
| Non-saturable loss A | A _{ns} = 15 % |
| Saturation fluence | $\Phi_{sat} = 120 \ \mu J/cm^2$ |
| Relaxation time constant t | t = 9 ps |
| Damage threshold | $\Phi = 1 \text{ mJ/cm}^2$ |
| Chip area 4 | 4.0 mm x 4.0 mm; other dimensions on request |
| Chip thickness 4 | 450 µm |
| Protection t | the SAM is protected with a dielectric front layer |
| x = 12.7 g | pe of mounting as follows: unmounted glued on a gold plated Cu-cylinder with 12.7 mm \emptyset glued on a gold plated Cu-cylinder with 25.4 mm \emptyset |

| 0 | |
|-------------------|--|
| x = 25.4 g | glued on a gold plated Cu-cylinder with 25.4 mm $arnothing$ |
| x = 12.7 s | soldered on a gold plated Cu-cylinder with 12.7 mm $arnothing$ |
| x = 25.4 s | soldered on a gold plated Cu-cylinder with 25.4 mm $arnothing$ |
| x = FC | mounted on a 1 m monomode fiber cable with FC connector |

Low intensity spectral reflectance

